ECE 113A Professor Burke (15400) Section A Homework #5 Solutions and Grading Criteria

A voltage V_A of 0.4144V is being applied to a step junction with n and p side dopings of $N_A = 10^{15}$ cm⁻³ and $N_D = 10^{15}$ cm⁻³, respectively. $n_i = 10^{10}$ cm⁻³.

Under equilibrium conditions: $p_{p,o} = N_A = 10^{15} \text{ cm}^{-3}$ $n_{p,o} = n_i^2 / N_A = 10^5 \text{ cm}^{-3}$ $n_{n,o} = N_D = 10^{15} \text{ cm}^{-3}$ $p_{n,o} = n_i^2 / N_D = 10^5 \text{ cm}^{-3}$

For depletion region boundaries: $\Delta n_p(-x_p) = (n_i^2/N_A)(exp[qV_A/kT] - 1) = (10^5 cm^{-3})(exp[0.4144V/0.259V] - 1) = 8.92x10^{11} cm^{-3}$ $\Delta p_n(x_n) = (n_i^2/N_D)(exp[qV_A/kT] - 1) = (10^5 cm^{-3})(exp[0.4144V/0.259V] - 1) = 8.92x10^{11} cm^{-3}$ $n_p = n_{p,o} + \Delta n_p(-x_p) exp[-x''/L_N] = p_{n,o} + \Delta p_n(x_n) exp[-x'/L_P]$

1) Calculate p on the p side at the interface. (6 pts)

Since $\Delta n_p(-x_p) \ll p_{p,o}$, low-level injection prevails. Therefore, the majority carrier concentration is approximately unchanged.

 $p_p = p_{p,o} = 10^{15} cm^{-3} \quad (exact answer required or no credit)$ 2) Calculate p on the p side 10 diffusion lengths away from the interface. (6 pts) $p_p = p_{p,o} = 10^{15} cm^{-3} \quad (exact answer required or no credit)$

- 3) Calculate p on the p side 20 diffusion lengths away from the interface. (6 pts) $p_p = p_{p,o} = 10^{15} cm^{-3}$ (exact answer required or no credit)
- 4) Calculate p on the p side 30 diffusion lengths away from the interface. (6 pts) $p_p = p_{p,o} = 10^{15} \text{ cm}^{-3}$ (exact answer required or no credit)
- 5) Calculate n on the p side at the interface. (6 pts)

$$n_p = n_{p,o} + \Delta n_p(-x_p) \exp[0]$$

= 10⁵ cm⁻³ + 8.92x10¹¹ cm⁻³
= 8.92x10¹¹ cm⁻³ (8-10 x 10¹¹ cm⁻³ for credit)

6) Calculate n on the p side 10 diffusion lengths away from the interface. (6 pts)

$$n_p = n_{p,o} + \Delta n_p(-x_p) \exp[-10]$$

= 10⁵ cm⁻³ + 8.92x10¹¹ cm⁻³ exp[-10]
= 4.06x10⁷ cm⁻³ (3-5 x 10⁷ cm⁻³ for credit)

7) Calculate n on the p side 20 diffusion lengths away from the interface. (6 pts)

$$n_p = n_{p,o} + \Delta n_p(-x_p) \exp[-20]$$

= 10⁵ cm⁻³ + 8.92x10¹¹ cm⁻³ exp[-20]
= 1.02x10⁵ cm⁻³ (0.8-1.2 x 10⁵ cm⁻³ for credit)

8) Calculate n on the p side 30 diffusion lengths away from the interface. (6 pts)

$$n_p = n_{p,o} + \Delta n_p(-x_p) \exp[-30]$$

$$= 10^{5} cm^{-3} + 8.92 x 10^{11} cm^{-3} exp[-30]$$

= 10⁵ cm⁻³ (exact answer required or no credit)

9) Calculate p on the n side at the interface. (6 pts)

$$p_n = p_{n,o} + \Delta p_n(x_n) \exp[0]$$

= 10⁵ cm⁻³ + 8.92x10¹¹ cm⁻³
= 8.92x10¹¹ cm⁻³ (8-10 x 10¹¹ cm⁻³ for credit)

10) Calculate p on the n side 10 diffusion lengths away from the interface. (6 pts)

 $p_n = p_{n,o} + \Delta p_n(x_n) \exp[-10]$ = 10⁵ cm⁻³ + 8.92x10¹¹ cm⁻³ exp[-10] = 4.06x10⁷ cm⁻³ (3-5 x 10⁷ cm⁻³ for credit)

11) Calculate p on the n side 20 diffusion lengths away from the interface. (6 pts)

 $p_n = p_{n,o} + \Delta p_n(x_n) \exp[-20]$ = 10⁵ cm⁻³ + 8.92x10¹¹ cm⁻³ exp[-20] = 1.02x10⁵ cm⁻³ (0.8-1.2 x 10⁵ cm⁻³ for credit)

12) Calculate p on the n side 30 diffusion lengths away from the interface. (6 pts)

$$p_n = p_{n,o} + \Delta p_n(x_n) \exp[-30] \\= 10^5 \text{ cm}^{-3} + 8.92 \times 10^{11} \text{ cm}^{-3} \exp[-30] \\= 10^5 \text{ cm}^{-3} \quad (\text{ exact answer required or no credit})$$

13) Calculate n on the n side at the interface. (6 pts) Since $\Delta p_n(x_n) \ll n_{n,o}$, low-level injection prevails. Therefore, the majority carrier concentration is approximately unchanged.

 $n_n = n_{n,o} = 10^{15} \text{ cm}^{-3}$ (exact answer required or no credit)

- 14) Calculate n on the n side 10 diffusion lengths away from the interface. (6 pts) $n_n = n_{n,o} = 10^{15} \text{ cm}^{-3}$ (exact answer required or no credit)
- 15) Calculate n on the n side 20 diffusion lengths away from the interface. (6 pts) $n_n = n_{n,o} = 10^{15} \text{ cm}^{-3}$ (exact answer required or no credit)
- 16) Calculate n on the n side 30 diffusion lengths away from the interface. (6 pts) $n_n = n_{n,o} = 10^{15} \text{ cm}^{-3}$ (exact answer required or no credit)
- 17) Make a dimensioned log(p or n) versus x sketch of both the majority and minority carrier concentrations in the quasineutral regions of the device (4 pts)

(If any answer in #1-16 are wrong, no points for this section. No partial credit.)

